Mauro Mosca

List of Publications by Year in descending order

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Μλυρο Μοςςλ

#	Article	IF	CITATIONS
1	Current status of AlInN layers lattice-matched to GaN for photonics and electronics. Journal Physics D: Applied Physics, 2007, 40, 6328-6344.	1.3	304
2	Midinfrared intersubband absorption in lattice-matched AlInNâ^•GaN multiple quantum wells. Applied Physics Letters, 2005, 87, 111106.	1.5	81
3	Stability/instability of conductivity and work function changes of ITO thin films, UV-irradiated in air or vacuum. Synthetic Metals, 2001, 122, 87-89.	2.1	72
4	Indium surfactant effect on AlNâ^•GaN heterostructures grown by metal-organic vapor-phase epitaxy: Applications to intersubband transitions. Applied Physics Letters, 2006, 88, 151902.	1.5	52
5	Correlation between <i>in situ</i> structural and optical characterization of the semiconductor-to-metal phase transition of VO ₂ thin films on sapphire. Nanoscale, 2020, 12, 851-863.	2.8	40
6	Multilayer (Al,Ga)N Structures for Solar-Blind Detection. IEEE Journal of Selected Topics in Quantum Electronics, 2004, 10, 752-758.	1.9	27
7	Lattice-Matched GaN–InAlN Waveguides at \$lambda=1.55 mu\$m Grown by Metal–Organic Vapor Phase Epitaxy. IEEE Photonics Technology Letters, 2008, 20, 102-104.	1.3	25
8	Generation of white LED light by frequency downconversion using perylene-based dye. Electronics Letters, 2012, 48, 1417.	0.5	21
9	In situ monitoring of pulsed laser indium–tin-oxide film deposition by optical emission spectroscopy. Spectrochimica Acta, Part B: Atomic Spectroscopy, 2001, 56, 743-751.	1.5	20
10	Defect incorporation in In-containing layers and quantum wells: experimental analysis via deep level profiling and optical spectroscopy. Journal Physics D: Applied Physics, 2021, 54, 025108.	1.3	20
11	Enhancement of photoconversion efficiency in dye-sensitized solar cells exploiting pulsed laser deposited niobium pentoxide blocking layers. Thin Solid Films, 2015, 574, 38-42.	0.8	18
12	Effects of the buffer layers on the performance of (Al,Ga)N ultraviolet photodetectors. Journal of Applied Physics, 2004, 95, 4367-4370.	1.1	17
13	The Effect of Nb Incorporation on the Electronic Properties of Anodic HfO ₂ . ECS Journal of Solid State Science and Technology, 2017, 6, N25-N31.	0.9	15
14	Internal photoemission in solar blind AlGaN Schottky barrier photodiodes. Applied Physics Letters, 2005, 86, 063511.	1.5	14
15	Solar blind detectors based on AlGaN grown on sapphire. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 964-971.	0.8	12
16	Progress in Violet Light-Emitting Diodes Based on ZnO/GaN Heterojunction. Electronics (Switzerland), 2020, 9, 991.	1.8	12
17	A simple apparatus for the determination of the optical constants and the thickness of absorbing thin films. Optics Communications, 2001, 191, 295-298.	1.0	11
18	Frequency-Downconversion Stability of PMMA Coatings in Hybrid White Light-Emitting Diodes. Journal of Electronic Materials, 2016, 45, 682-687.	1.0	11

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#	Article	IF	CITATIONS
19	Warm white LED light by frequency down-conversion of mixed yellow and red Lumogen. Proceedings of SPIE, 2013, , .	0.8	9
20	Low-temperature growth of <i>n</i> ⁺⁺ -GaN by metalorganic chemical vapor deposition to achieve low-resistivity tunnel junctions on blue light emitting diodes. Semiconductor Science and Technology, 2019, 34, 015002.	1.0	9
21	Current Spreading Length and Injection Efficiency in ZnO/GaN-Based Light-Emitting Diodes. IEEE Transactions on Electron Devices, 2019, 66, 4811-4816.	1.6	6
22	Effects of the process conditions on the plume of a laser-irradiated indium–tin-oxide target. Optics Communications, 2001, 197, 341-354.	1.0	4
23	Effects of 5 MeV electron irradiation on deep traps and electroluminescence from near-UV InGaN/GaN single quantum well light-emitting diodes with and without InAlN superlattice underlayer. Journal Physics D: Applied Physics, 2020, 53, 445111.	1.3	4
24	Well-aligned hydrothermally synthesized zinc oxide nanorods on p-gan without a seed layer. , 2015, , .		3
25	Microcavity Light Emitting Diodes Based on GaN membranes Grown by Molecular Beam Epitaxy on Silicon. Japanese Journal of Applied Physics, 2003, 42, 118-121.	0.8	2
26	Analysis of Transition Metal Oxides based Heterojunction Solar Cells with S-shaped J-V curves. , 2020, ,		2
27	Density of states characterization of TiO2 films deposited by pulsed laser deposition for heterojunction solar cells. Nano Research, 2022, 15, 4048-4057.	5.8	1